



2SK536

Features

- Large $|Y_{fs}|$
- Enhancement type
- Small ON resistance

Absolute Maximum Ratings at Ta=25°C

			unit
Drain to Source Voltage	V_{DS}	50	V
Gate to Source Voltage	V_{GS}	±12	V
Drain Current	I_D	100	mA
Drain Current(Pulse)	I_{DP}	300	mA
Allowable Power Dissipation	P_D	200	mW
Channel Temperature	T_{ch}	125	°C
Storage Temperature	T_{stg}	-55 to +125	°C

Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Drain to Source Breakdown Voltage	$V_{(BR)DS}$	$I_D=10\mu A, V_{GS}=0V$	50			V
Gate Cutoff Current	I_{GSS}	$V_{GS}=10V, V_{DS}=0V$		0.01	10	nA
Cutoff Voltage	$I_{GS(off)}$	$V_{DS}=10V, I_D=100\mu A$	0.3	0.9	1.5	V
Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$			1	μA
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS}=10V, I_D=50mA, f=1kHz$	25	40		mS
Input Capacitance	c_{iss}	$V_{DS}=10V, V_{GS}=0, f=1MHz$		15		pF
Output Capacitance	c_{oss}	$V_{DS}=10V, V_{GS}=0, f=1MHz$		6		pF
Reverse Transfer Capacitance	c_{rss}	$V_{DS}=10V, V_{GS}=0, f=1MHz$		0.5		pF
ON Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=10mA$		20		Ω

Package Dimensions 2024A (unit:mm)

